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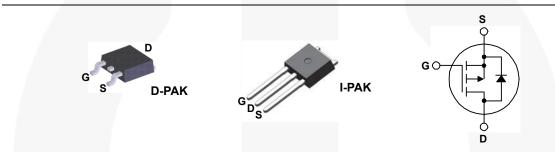
FQD8P10 / FQU8P10 P-Channel QFET[®] MOSFET -100 V, -6.6 A, 530 mΩ

Description

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- 6.6 A, -100 V, R_{DS(on)} = 530 m Ω (Max) @ V_{GS} = -10 V, I_D = -3.3 A
- Low Gate Charge (Typ. 12 nC)
- Low Crss (Typ. 30 pF)
- 100% Avalanche Tested



Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

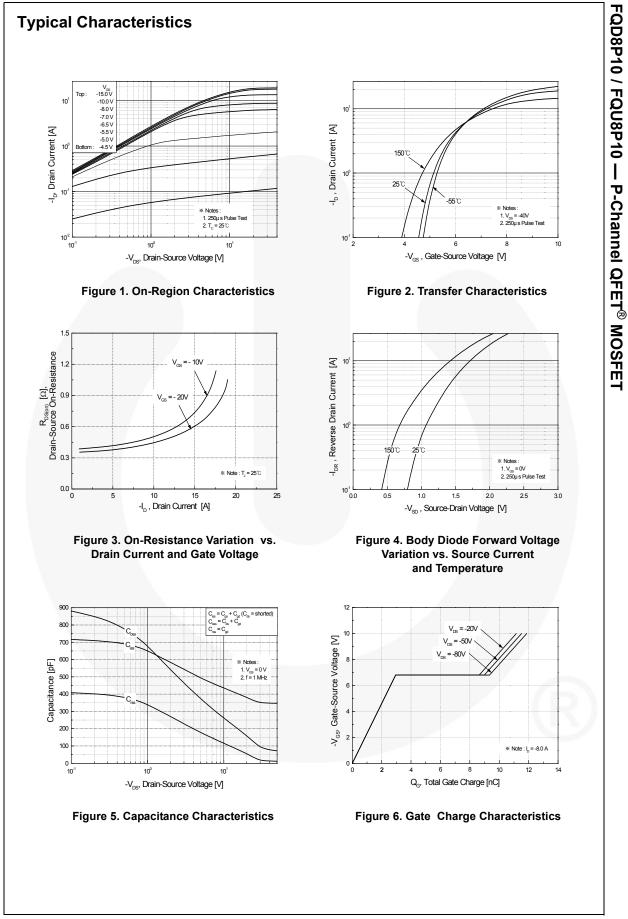
Symbol	Parameter		FQD8P10TM / FQU8P10TU	Unit	
V _{DSS}	Drain-Source Voltage			-100	V
I _D	Drain Current	- Continuous (T _C = 25°	°C)	-6.6	А
		- Continuous (T _C = 100)°C)	-4.2	A
Ы	Drain Current	- Pulsed	(Note 1)	-26.4	A
V _{GSS}	Gate-Source Voltage			± 30	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		150	mJ	
I _{AR}	Avalanche Current		(Note 1)	-6.6	A
E _{AR}	Repetitive Avalanche Energy		(Note 1)	4.4	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		-6.0	V/ns	
P _D	Power Dissipation (T _A = 25°C) *			2.5	W
	Power Dissipati	on (T _C = 25°C)	44	W	
		- Derate above 25°C		0.35	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range			-55 to +150	°C
TL	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds			300	°C

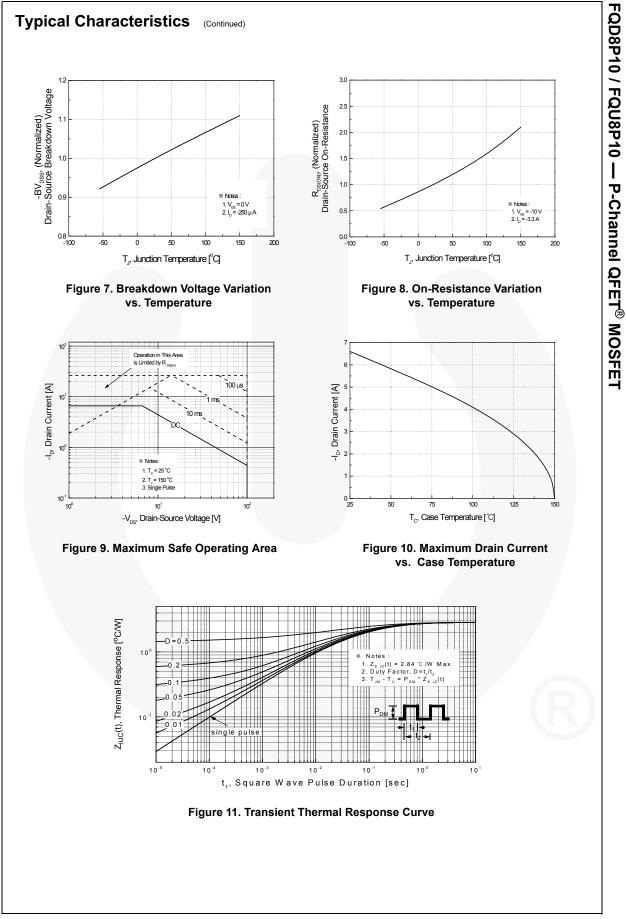
Thermal Characteristics

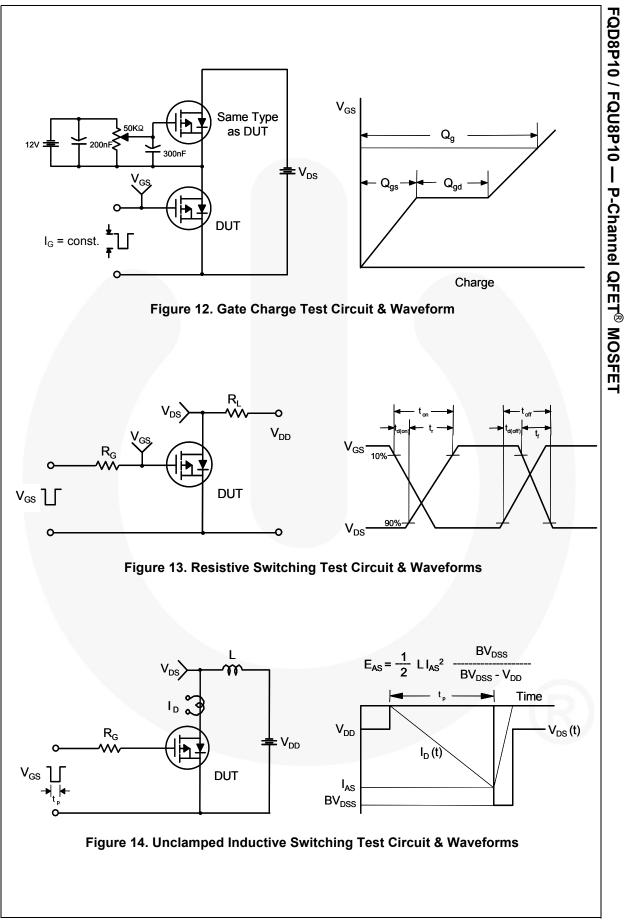
Symbol	Parameter	FQD8P10TM FQU8P10TU	Unit
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	2.84	
Р	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	110	°C/W
$R_{ ext{ heta}JA}$	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	50	

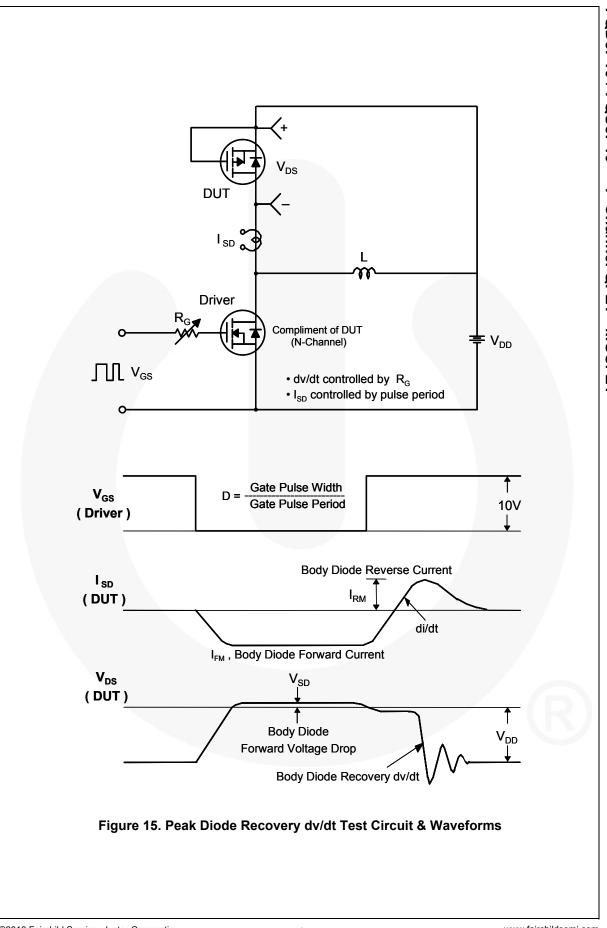
November 2013

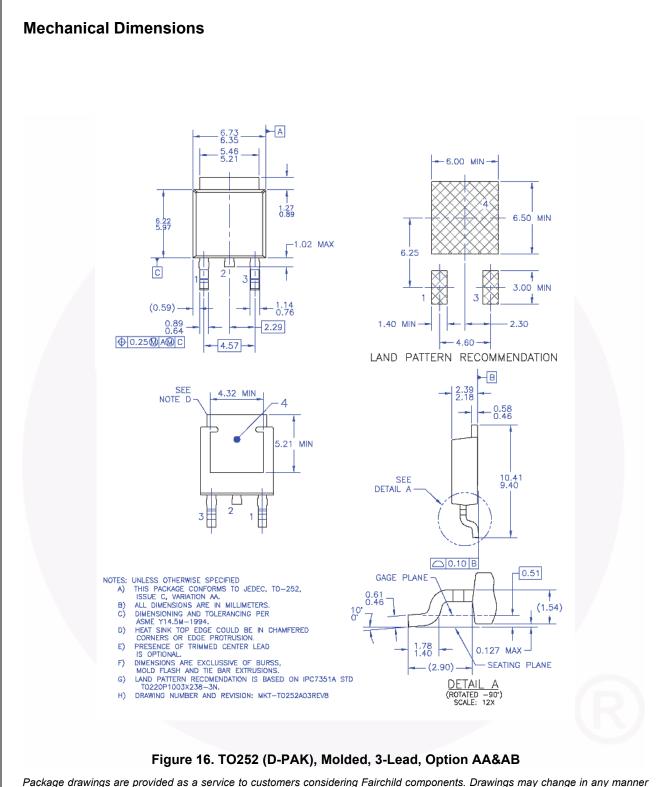
Part Number FQD8P10TM		Top Mark	Packa	kage Packing Method Ree		Reel	Size	Tape Width 16 mm		Quantity 2500 units	
		FQD8P10	D-PA	K Tape	Tape and Reel		mm				
FQU8P10TU FQU8P10 I-F		I-PA	AK Tube N/		N/.	A N/A			70 units		
lectri	cal Cha	racteristics T _c =	25°C unle	ss otherwise noted.							
Symbol	ibol Parameter			Test Conditions			Min	Тур	Max	Unit	
Off Cha	racterist	ics									
BV _{DSS}		rce Breakdown Voltage		V _{GS} = 0 V, I _D = -	250 μΑ		-100			V	
ΔBV _{DSS} ΔT _{.1}	Breakdown Voltage Temperature Coefficient			$I_D = -250 \ \mu\text{A}$, Referenced to 25°C				-0.1		V/°C	
DSS	7 0 1			V _{DS} = -100 V, V _{GS} = 0 V					-1	μA	
	∠ero Gate	Voltage Drain Current		$V_{DS} = -80 \text{ V}, \text{ T}_{C} = 125^{\circ}\text{C}$					-10	μA	
GSSF	Gate-Body	Gate-Body Leakage Current, Forward		$V_{GS} = -30 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$					-100	nA	
GSSR	Gate-Body	/ Leakage Current, Rev	/erse	V_{GS} = 30 V, V_{DS}	= 0 V				100	nA	
0n 04 -	re etc ris ti										
Un Cha V _{GS(th)}	Gate Three	I CS shold Voltage		$V_{DS} = V_{GS}, I_D =$	-250	_	-2.0		-4.0	V	
R _{DS(on)}	Static Drai On-Resista	n-Source		V _{GS} = -10 V, I _D =			-2.0	0.41	0.53	Ω	
9 _{FS}		ransconductance		V _{DS} = -40 V, I _D =	-3.3 A			4.1		S	
	c Charac	teristics									
C _{iss}	Input Capa			V _{DS} = -25 V, V _{GS}	= 0 V			360	470	pF	
C _{oss}	Output Ca			f = 1.0 MHz	; - U V ,			120	155	pF	
C _{rss}	Reverse T	ransfer Capacitance						30	40	pF	
	0										
	-							11	20		
t _{d(on)} t	Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time			V_{DD} = -50 V, I _D = -8.0 A, R _G = 25 Ω				11	30	ns	
t _r								110 20	230 50	ns ns	
^t d(off) t _f	Turn-Off F	,			(1	Note 4)		35	80	ns	
q Q _g	Total Gate				0.0.4			12	15	nC	
Q _{gs}		ce Charge		$V_{DS} = -80 V, I_{D} =$	-8.0 A,			3.0		nC	
Q _{gd}	Gate-Drair			V _{GS} = -10 V	(Note 4)		6.4		nC	
gu	Cuto Dian	i ondigo				,		0.1		no	
Drain-S	ource Di	ode Characteristi	cs and	d Maximum F	Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current						-6.6	Α			
SM	Maximum Pulsed Drain-Source Diode F			Forward Current					-26.4	А	
V _{SD}	Drain-Sou	Drain-Source Diode Forward Voltage		V_{GS} = 0 V, I _S = -6.6 A					-4.0	V	
t _{rr}	Reverse R	ecovery Time		$V_{GS} = 0 V, I_{S} = -1$				98		ns	
Q _{rr}	Reverse Recovery Charge			dI _F / dt = 100 A/µs				0.35		μC	







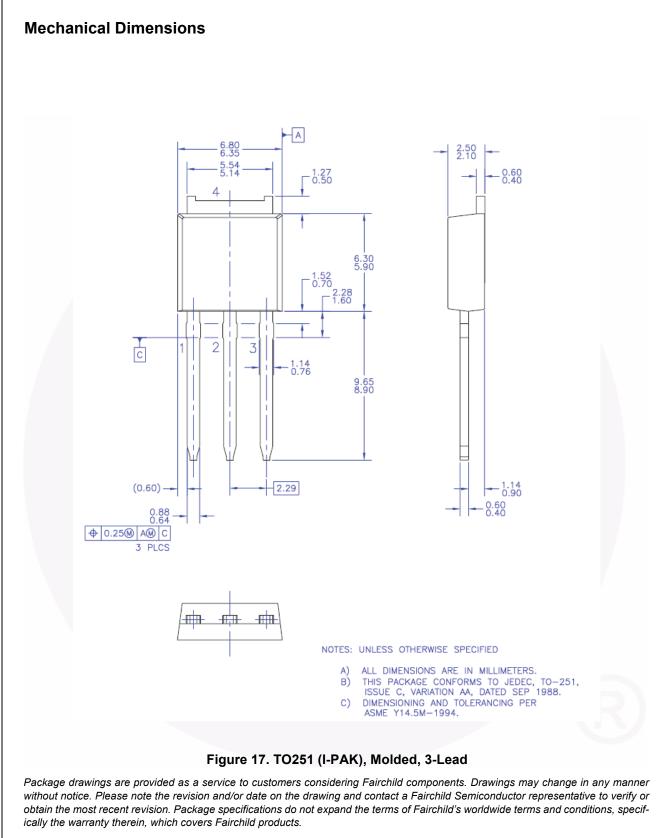




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FQD8P10 / FQU8P10 — P-Channel QFET[®] MOSFET



No Identification Needed

Obsolete

Full Production

Not In Production

Datasheet contains specifications on a product that is discontinued by Fairchild

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Rev. 166

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